

1700V N-Channel Silicon Carbide Power MOSFET

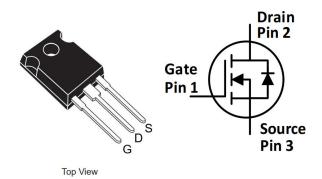
Features:

- · Low on-resistance
- · Fast switching speed with low capacitances
- Fast intrinsic diode with low reverse recovery (Q_{RR})
- · Halogen-free, RoHS compliant

Applications:

- · Motor drives
- DC/DC converters
- · Switched mode power supplies
- · Solar inverters

Package:



Part Number	Package		
DTN055N170SC3	TO247-3		

Absolute Maximum Ratings (Tc=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions
$V_{ extsf{DS}}$	Drain-Source voltage	1700	V	V _{GS} =0V, I _D =100μA
V_{GS}	Gate-Source voltage	-10 to 22	V	Recommended maximum
	Drain current (continuous)	5.5	Α	T _c =25°C
l _D		4	Α	Tc=100°C
I _{DM}	Drain current (pulsed)	11	Α	Pulse width limited by SOA
Ртот	Total power dissipation	100	W	T _c =25°C
T_{stg}	Storage temperature range	-55 to 175	°C	
Т	Operating junction temperature	-55 to 175	°C	
Τι	Solder Temperature	260	°C	

Thermal Data

Symbol Parameter		Value	Unit
R _{θ(J-C)} Thermal Resistance from Junction to Case		1.5	°C/W

Rev.1.0



Electrical Characteristics (T_c=25°C unless otherwise specified)

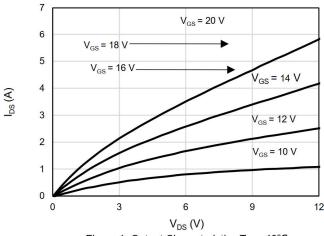
Symbol	Parameter	Value			Unit	Test Conditions
•		Min.	Тур.	Max.		
l _{DSS}	Zero gate voltage drain current		5	50	μΑ	V _{DS} =1700V, V _{GS} =0V
GSS	Gate leakage current		1	±100	nA	V _{DS} =0V, V _{GS} =-10~22V
			3.2		V	V _{GS} =V _{DS} , I _D =0.7mA
V_{TH}	Gate threshold voltage		2			V _{GS} =V _{DS} , I _D =0.7mA @ T _C =175°C
D.	Static drain-source on- resistance		1000	1500	mΩ	V _{GS} =18V, I _D =2A @T _J =25°C
Ron			2100		mΩ	V _{GS} =18V, I _D =2A @T _J =175°C
Ciss	Input capacitance		184		pF	
C_{oss}	Output capacitance		12		pF	V _{DS} =1000V, V _{GS} =0V,
C_{rss}	Reverse transfer capacitance		3		pF	f=100kHz, V _{AC=} 25mV
E _{oss}	Coss stored energy		7		μJ]
Qg	Total gate charge		16.5		nC	V -1200V I -14
Q_{gs}	Gate-source charge		2.5		nC	$V_{DS}=1200V, I_{D}=1A,$ $V_{GS}=-6 \text{ to } 18V$
$Q_{\text{gd}} \\$	Gate-drain charge		12		nC	V650 to 10V
R_g	Gate input resistance		8.7		Ω	f=1MHz
Eon	Turn-on switching energy		45		μЈ	
E _{OFF}	Turn-off switching energy		21		μJ	$V_{DS}=1200V, I_{D}=2A,$
t _{d(on)}	Turn-on delay time		5			V _{GS} =-6 to 18V,
t _r	Rise time		8		nc	$R_{G(ext)}=2.5\Omega$,
t _{d(off)}	Turn-off delay time		6		ns	L=1000μH
t _f	Fall time		41			

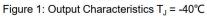


Reverse Diode Characteristics (T_c=25°C unless otherwise specified)

Symbol	Parameter	Value			Unit	Test Conditions
		Min.	Тур.	Max.		
	V _{SD} Diode forward voltage		3.8		V	I _{SD} =1A, V _{GS} =-4V
V_{SD}		3.5		\/	I _{SD} =1A, V _{GS} =-4V,	
			3.3		V	T ₁ =175°C
t _{rr}	Reverse recovery time		15		ns	V _{GS} =-4V
	Doverse recovery charge		68		nC	$I_{SD}=2 A, V_{R}=1200V,$
Qrr	Reverse recovery charge		00		TIC	di/dt=2350A/us,
I _{RRM}	Peak reverse recovery current		5		Α	T _J =175°C

Typical Performance (curves)





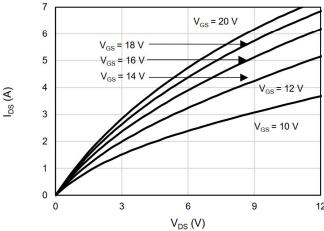


Figure 2: Output Characteristics $T_J = 25^{\circ}C$

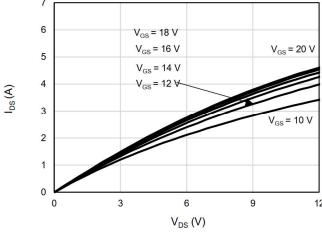
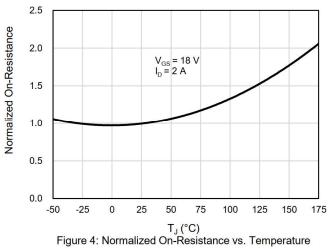
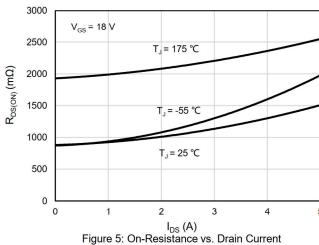


Figure 3: Output Characteristics $T_J = 175^{\circ}C$





For Various Temperatures

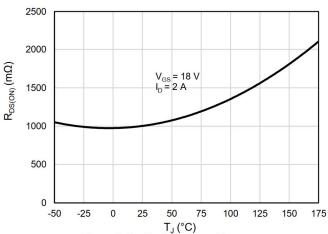


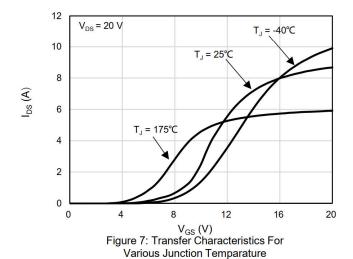
Figure 6: On-Resistance vs. Temperature For Various Gate Voltage

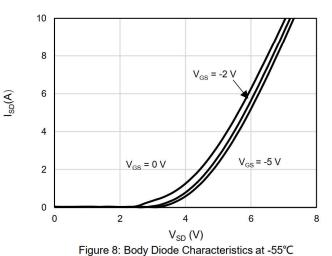
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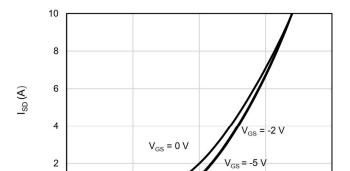
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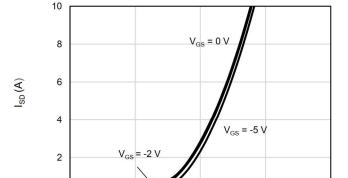
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Typical Performance (curves)









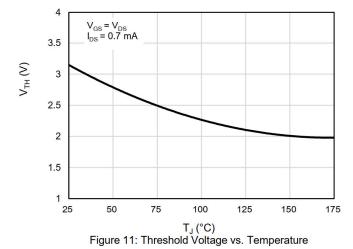
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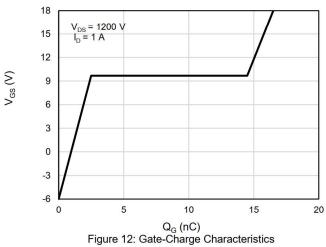
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V_{SD} (V) Figure 9: Body Diode Characteristics at 25°C

6

 $V_{SD}(V)$ Figure 10: Body Diode Characteristics at 175°C









Typical Performance (curves)

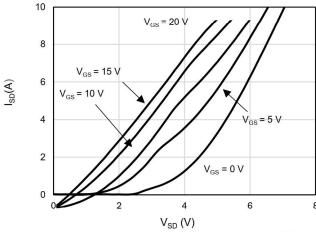


Figure 13: 3rd Quadrant Characteristics at -55°C

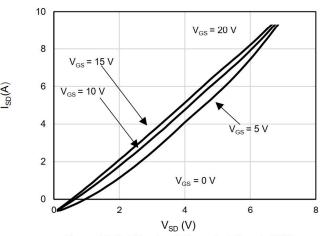


Figure 14: 3rd Quadrant Characteristics at 25°C

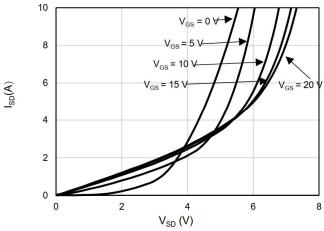
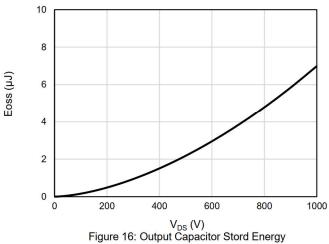
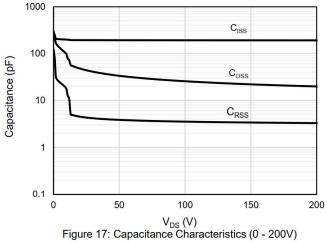
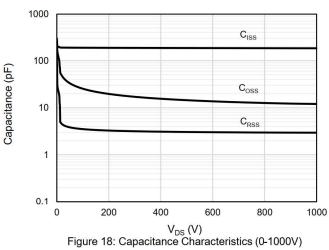


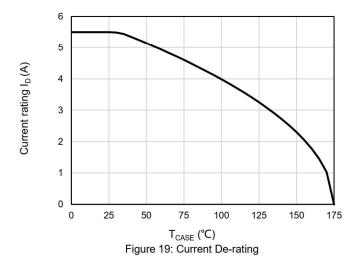
Figure 15: 3rd Quadrant Characteristics at 175°C

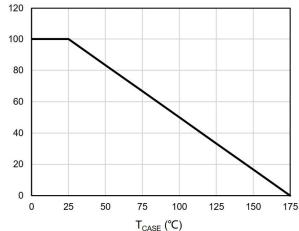






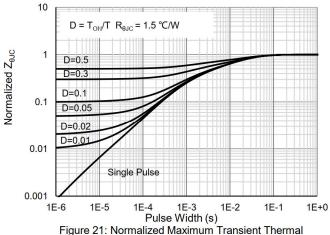
Typical Performance (curves)

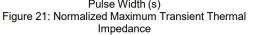


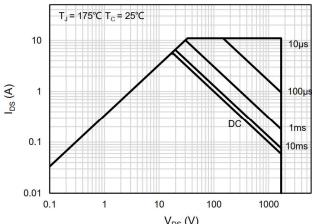


 $P_D(W)$

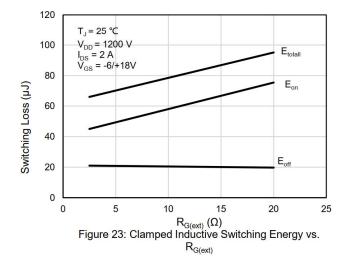
Figure 20: Maximum Power Disspation Derating vs CaseTemperature







 $V_{\rm DS}\left(V\right)$ Figure 22: Maximum Forward Biased Safe Operating Area



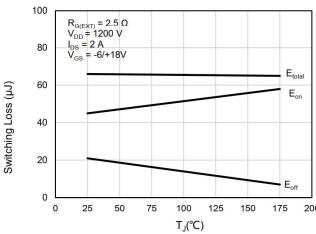
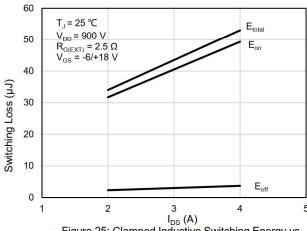


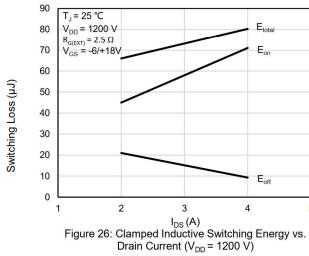
Figure 24: Clamped Inductive Switching Energy vs. T_J

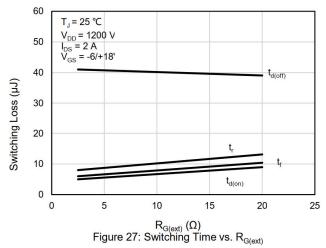


Typical Performance (curves)



 I_{DS} (A) Figure 25: Clamped Inductive Switching Energy vs. Drain Current (V_{DD} = 600 V)





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